

**1. Material**  
 Substrate GaP (N Type)  
 Epitaxial Layer GaP (P/N Type)

**2. Electrode**  
 N(Cathode) Side Gold Alloy  
 P(Anode) Side Gold Alloy

**3. Electro-Optical Characteristics**

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.8		V	IF=1mA
	$V_{F(2)}$		2.25	2.4	V	IF=20mA
Reverse Voltage	$V_R$	8			V	IR=10uA
Brightness	Iv	30	35		mcd	IF=20mA
Wavelength	$\lambda_d$		635		nm	IF=20mA
	$\Delta\lambda$		100		nm	IF=20mA

※ Note : Brightness is measured by Sorter E/T system with bare chip.

**4. Mechanical Data**

(a) Emission Area	-----	10mil x 10mil
(b) Bottom Area	-----	11mil x 11mil
(c) Bonding Pad	-----	115um
(d) Chip Thickness	-----	11mil
(e) Junction Height	-----	6.8mil

